

13 NOV 2002

2002068047

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
17 October 2002 (17.10.2002)

PCT

(10) International Publication Number
WO 02/082184 A1

(51) International Patent Classification⁷: **G03F 7/004**,
C08F 30/08, 16/12, C08G 77/20, 77/04, 77/00

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(21) International Application Number: PCT/US02/10639

(22) International Filing Date: 4 April 2002 (04.04.2002)

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(25) Filing Language: English

(26) Publication Language: English

(81) Designated States (*national*): JP, KR, SG.

(30) Priority Data:
60/281,295 4 April 2001 (04.04.2001) US

(84) Designated States (*regional*): European patent (AT, BE,
CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC,
NL, PT, SE, TR).

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Published:
— with international search report
— with amended claims

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For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.



162162



ACTION

WO 02/082184 A1

(54) Title: SILICON-CONTAINING ACETAL PROTECTED POLYMERS AND PHOTORESISTS COMPOSITIONS THEREOF

(57) Abstract: A photoresist composition comprising at least one acetal polymer having a silicon substituent; provided that the silicon substituent is not directly attached to the acetal functionality, thereby providing high resolution, improved DOF, and improved dimensional stability under metrology conditions.